

Amendments to the Claims

Claims 1-26 (Cancelled).

- 5 27. (Presently Amended) An electron lens for an electron emitter, comprising:
a focusing lens layer; and
a polymer spacer layer between the focusing lens layer and the
electron emitter wherein the polymer spacer layer defining at least one
opening having an undercut of about 1 micron to about 2 microns per about
10 6.5 microns of depth.

28. (Original) The electron lens of claim 27 wherein the polymer spacer material is between about 2 microns and about 12 microns thick.

- 15 29. (Original) The electron lens of claim 27 wherein the polymer spacer layer has been cured to remove volatile content.

30. (Original) A focused electron emitter comprising the electron lens of claim 27.

- 20 31. (Original) An electronic device comprising at least one electron lens of claim 27.

- 25 32. (Currently Amended) A focused [metal insulator semiconductor] emitter, comprising:

a tunneling layer less than about 500 angstroms in thickness disposed on a semiconductor substrate;

- a polymer spacer layer disposed on the semiconductor substrate and defining a first opening, having an undercut of about 1 micron to about 2
30 microns per about 6.5 microns of depth, disposed over the tunneling layer;

a focusing lens layer disposed on the polymer spacer layer and defining a second opening disposed over the tunneling layer; and

a cathode layer disposed on the tunneling layer.

33. (Currently Amended) The [electron lens]focused emitter of claim 32 wherein the polymer spacer [material]layer is between about 2 microns and about 12 microns thick.

5 34. (Currently Amended) The [electron lens]focused emitter of claim 32 wherein the polymer spacer layer has been cured to remove volatile content.

35. (Currently amended) An electronic device comprising at least one [electron lens]focused emitter of claim 32.

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36. (Original) The electronic device of claim 35 wherein the electronic device is a display device.

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37. (Original) The electronic device of claim 35 wherein the electronic device is a mass storage device.

38. (Currently Amended) A focused electron emitter, comprising:
a tunneling layer less than about 500 angstroms in thickness;
means for focusing electrons emitted from tunneling layer; and
20 polymer means for spacing the means for focusing electrons from the tunneling layer wherein the polymer means has been cured to remove volatile components and defines an opening having an undercut of about 1 micron to about 2 microns per about 6.5 microns of depth.

25 39. (Original) The focused electron emitter of claim 38 wherein the tunneling layer is about 100 Angstroms.

40. (Original) The focused electron emitter of claim 38 wherein the means for focusing electrons and the polymer means for spacing have substantially the
30 same temperature expansion coefficient.